

Appln No. 09/423,401
Amdt date May 1, 2006
Reply to Office action of January 30, 2006

Amendments to the Specification:

Please replace paragraph on page 12, lines 22-25 with the following amended paragraph:

The dielectric layer may be made of any reactive dielectric material which contains basic elements of silicon ~~silicon~~ and oxygen, such as SiO_2 or silica, and may be deposited by any deposition method. This layer may also contain other elements such as N and F.